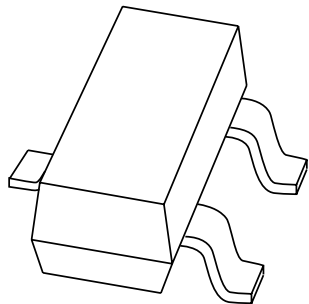


DATA SHEET



PMMT491A NPN BISS transistor

Product specification
Supersedes data of 1999 May 21

1999 Aug 04

NPN BISS transistor

PMMT491A

FEATURES

- High current (max. 1 A)
- Low collector-emitter saturation voltage ensures reduced power consumption.

APPLICATIONS

- Battery powered units where high current and low power consumption are important.

DESCRIPTION

NPN BISS (Breakthrough In Small Signal) transistor in a SOT23 plastic package. PNP complement: PMMT591A.

MARKING

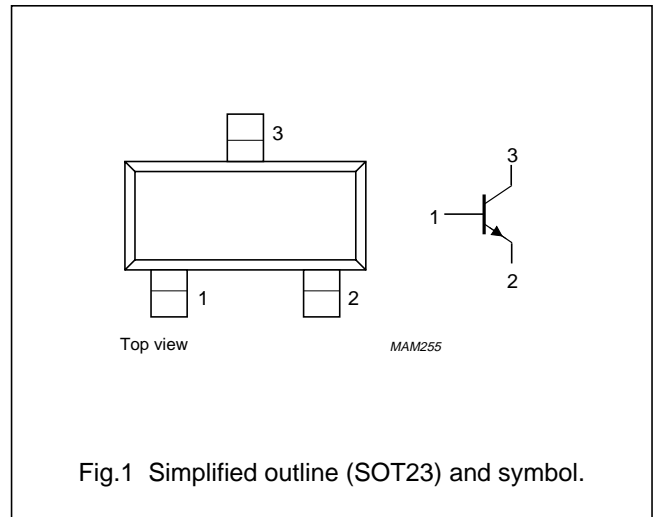
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMMT491A	9A*

Note

1. * = p: Made in Hong Kong.
* = t: Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	40	V
V _{CEO}	collector-emitter voltage	open base	–	40	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	1	A
I _{CM}	peak collector current		–	2	A
I _{BM}	peak base current		–	1	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN BISS transistor

PMMT491A

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	100	nA
I_{CEO}	collector cut-off current	$I_B = 0; V_{CE} = 30\text{ V}$	–	100	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}$; note 1 $I_C = 1\text{ mA}$ $I_C = 500\text{ mA}$ $I_C = 1\text{ A}$	300 300 200	– 900 –	
V_{CEsat}	collector-emitter saturation voltage	note 1 $I_C = 100\text{ mA}; I_B = 1\text{ mA}$ $I_C = 500\text{ mA}; I_B = 50\text{ mA}$ $I_C = 1\text{ A}; I_B = 100\text{ mA}$	– – –	200 300 500	mV mV mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$; note 1	–	1.2	V
V_{BE}	base-emitter voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$; note 1	–	1.1	V
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	10	pF
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	150	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

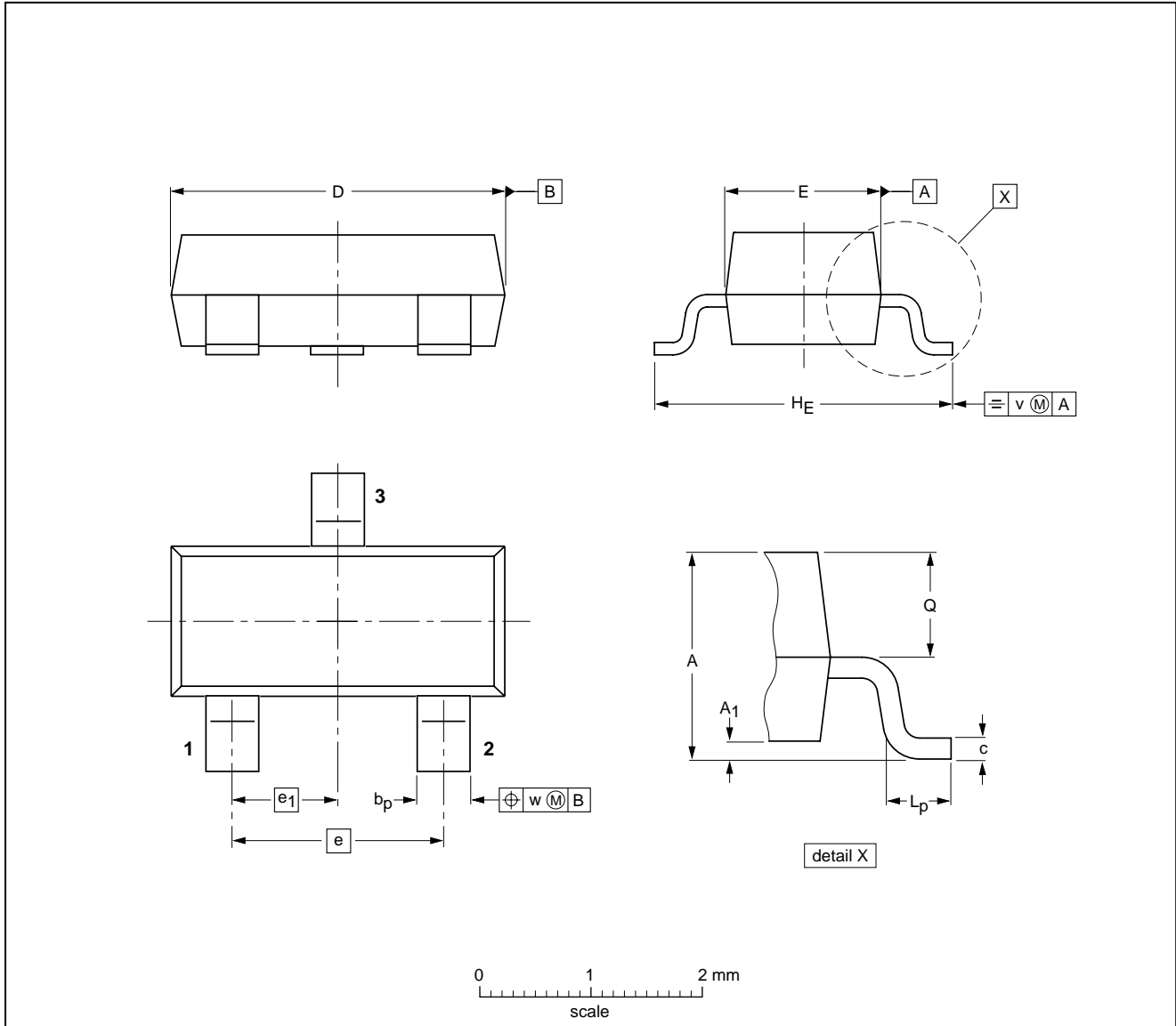
NPN BISS transistor

PMMT491A

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						97-02-28

NPN BISS transistor

PMMT491A

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

NPN BISS transistor

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NOTES

NPN BISS transistor

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NOTES

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